

Ultra Low Capacitance TVS/ESD Protection Diode

DESCRIPTION

SLESD0502L is an ultra-low capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With typical capacitance of 0.25pF (I/O to I/O) only, SLESD0502L is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 ($\pm 15\text{kV}$ air, $\pm 8\text{kV}$ contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc.

SLESD0502L uses small DFN1006-3L package. Each SLESD0502L device can protect two high-speed data lines. The combined features of low capacitance, small size and high ESD robustness make SLESD0502L ideal for high-speed data port and high-frequency line applications. The low clamping voltage of the SLESD0502L guarantees a minimum stress on the protected IC.

FEATURES

- ✧ Transient protection for high-speed data lines
 - IEC 61000-4-2 (ESD) $\pm 15\text{kV}$ (Air)
 - $\pm 8\text{kV}$ (Contact)
 - IEC 61000-4-4 (EFT) 40A (5/50 ns)
 - Cable Discharge Event (CDE)
- ✧ Small package (1.0mm×0.6mm×0.5mm)
- ✧ Protects two data lines
- ✧ Low capacitance: 0.2pF Typical (I/O-I/O)
- ✧ Low leakage current
- ✧ Low clamping voltage

MACHANICAL DATA

- ✧ DFN1006-3L package
- ✧ Flammability Rating: UL 94V-0
- ✧ Packaging: Tape and Reel
- ✧ High temperature soldering guaranteed:260/10s
- ✧ Reel size: 7 inch

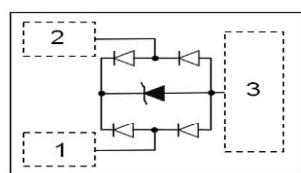
ORDERING INFORMATION

- ✧ Device: SLESD0502L
- ✧ Package: DFN1006-3L
- ✧ Marking: 52L
- ✧ Material: Halogen free
- ✧ Packing: Tape & Reel
- ✧ Quantity per reel: 10,000pcs

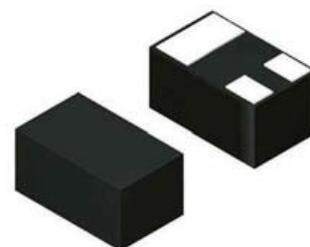
APPLICATIONS

- ✧ Serial ATA
- ✧ Desktops, Servers and Notebooks
- ✧ PCI Express
- ✧ MDDI Ports
- ✧ USB Data Line Protection
- ✧ Display Ports
- ✧ Digital Visual Interfaces (DVI)

PIN CONFIGURATION



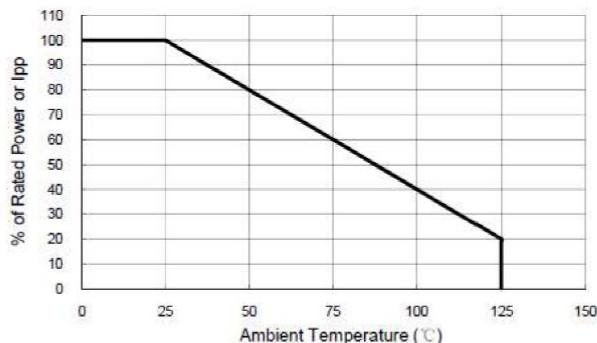
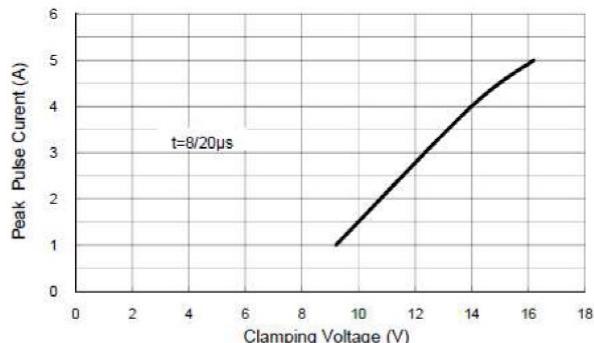
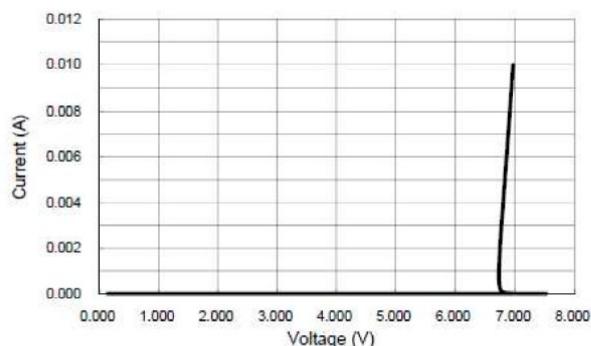
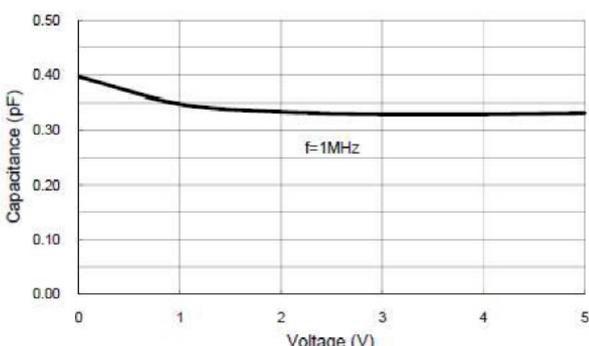
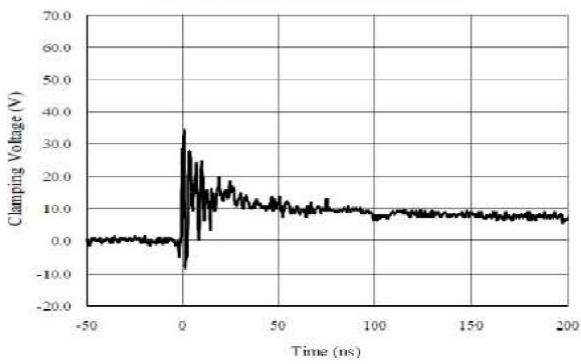
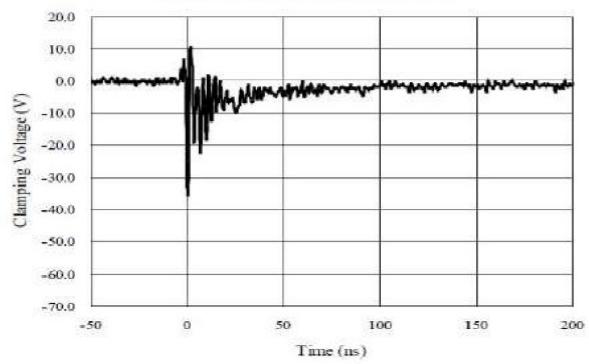
PACKAGE OUTLINE



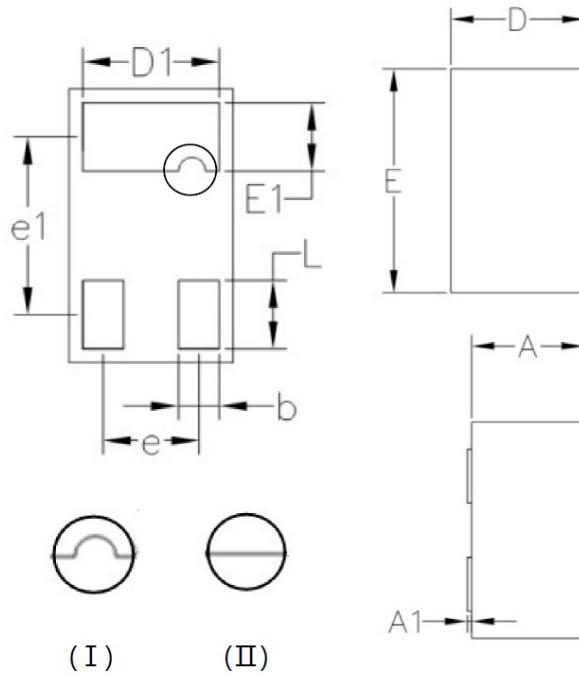
| ABSOLUTE MAXIMUM RATING | | | |
|-------------------------|--|------------|-------|
| Symbol | Parameter | Value | Units |
| P _{PP} | Peak Pulse Power (8/20μs) | 60 | W |
| V _{ESD} | ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact) | ±20 ±20 | kV |
| T _{OPT} | Operating Temperature | -55/+125 | °C |
| T _{STG} | Storage Temperature | -55/+150 | °C |

| ELECTRICAL CHARACTERISTICS (Tamb=25°C) | | | | | | |
|--|---------------------------|--|-----|-----|-----|-------|
| Symbol | Parameter | Test Condition | Min | Typ | Max | Units |
| V _{RWM} | Reverse Working Voltage | I/O to GND | | | 5.0 | V |
| V _{BR} | Reverse Breakdown Voltage | I _T = 1mA Between I/O and GND | 6.0 | | | V |
| I _R | Reverse Leakage Current | V _{RWM} = 5V Between I/O and GND | | | 100 | nA |
| V _C | Clamping Voltage | I _{PP} = 1A, t _p = 8/20μs Between I/O and GND | | | 10 | V |
| | | I _{PP} = 4A, t _p = 8/20μs Between I/O and GND | | | 15 | V |
| V _F | Forward Voltage | I _T = 10mA Between I/O and GND | | | 1.2 | V |
| C _T | Total Capacitance | V _R = 0V, f = 1MHz Between I/O and GND | | 0.4 | 0.6 | pF |
| | | V _R = 0V, f = 1MHz Between I/O and I/O | | 0.2 | 0.3 | pF |

ELECTRICAL CHARACTERISTICS CURVE

Fig 1 Power Derating Curve**Fig 2 Clamping Voltage vs Peak Pulse Current****Fig 3 Voltage Sweeping****Fig 4 Voltage vs Capacitance****Fig 5 ESD Clamping
(+8kV Contact per IEC 61000-4-2)****Fig 6 ESD Clamping
(-8kV Contact per IEC 61000-4-2)**

DFN1006-3L PACKAGE OUTLINE DIMENSIONS



| SYMBOL | DIMENSIONS IN MM | | |
|--------|------------------|------|------|
| | MIN | NOM | MAX |
| A | 0.45 | 0.50 | 0.55 |
| A1 | 0.00 | -- | 0.05 |
| D | 0.55 | 0.60 | 0.65 |
| E | 0.95 | 1.00 | 1.05 |
| D1 | 0.45 | 0.50 | 0.55 |
| E1 | 0.20 | 0.25 | 0.30 |
| L | 0.20 | 0.25 | 0.30 |
| b | 0.10 | 0.15 | 0.20 |
| e | 0.35BSC | | |
| e1 | 0.65BSC | | |